



ON Semiconductor®

ECH8655R

SPICE PARAMETER

Nch MOS FET

model : BSIM3V3.2

Parameter	Value	Parameter	Value	Parameter	Value
LEVEL	8				
VERSION	3.2	TNOM	27	TOX	3.3E-08
VTH0	0.96	K1	1.96	K2	-0.04
NLX	1.70E-07	DVT0	3.12	DVT1	0.58
DVT2	-0.01	U0	630	UA	2.20E-09
UB	1.00E-21	VSAT	1.75E+05	A0	0.26
AGS	-1	A1	0	A2	1
RDSW	8.25E+02	PRWG	7.00E-05	WR	0.82
WINT	0	LINT	0.00E+00	VOFF	-0.075
NFACTOR	0.76	CIT	0	CDSC	2.40E-04
CDSCD	0	ETA0	0.39	DSUB	1
PCLM	1.3	PDIBLC1	0.17	PDIBLC2	1.00E-05
DROUT	1	PSCBE1	1.50E+09	PSCBE2	1.00E-05
PVAG	0.01	DELTA	0.05	NGATE	1.00E+19
MOBMOD	1	NQSMOD	0	NOIMOD	1
CAPMOD	3	XPART	0.5	CGSO	1.00E-14
CGDO	1.00E-12	CGBO	0	CGSL	0
CGDL	1.00E-12	CKAPPA	1.2	CF	0
CLC	3.00E-09	CLE	0.8	DWC	0
DLC	-1.40E-13	NOFF	4	VOFFCV	-0.4
ACDE	1	MOIN	15	CJ	3.00E-04
MJ	0.48	PB	1.2	JS	2.40E-07
NJ	1	XTI	3	IJTH	0
KT1	-0.4	UTE	-0.2	PRT	2.00E+03
AT	3.30E+04				

Temp = 27 deg
 L = 1.0E-6 m
 W = 1365222E-6 m
 AD = 1365222E-12 m²
 RG = 120 ohm
 RB = 0.006 ohm

Date : 2013/03/11

*Information herein is for example only ;
 It is not guaranteed for volume production.

ON Semiconductor

